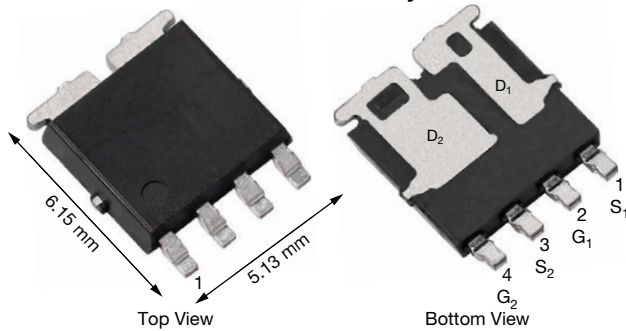


Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFETs

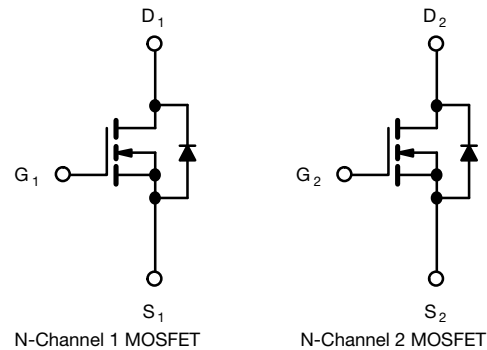
PowerPAK® SO-8L Dual Asymmetric

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Optimized for synchronous buck applications
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
V _{DS} (V)	60	60
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0200	0.0086
I _D (A)	20	54
Configuration	Dual	
Package	PowerPAK SO-8L asymmetric	



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT	
Drain-source voltage	V _{DS}	60	60	V	
Gate-source voltage	V _{GS}	± 20			
Continuous drain current	I _D	T _C = 25 °C	20 ^a	54	A
		T _C = 125 °C	15	31	
Continuous source current (diode conduction)	I _S	20 ^a	44	mJ	
Pulsed drain current ^b	I _{DM}	65	90		
Single pulse avalanche current	I _{AS}	19	31		
Single pulse avalanche energy	E _{AS}	18	48	W	
Maximum power dissipation ^b	P _D	T _C = 25 °C	27		48
		T _C = 125 °C	9	16	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175		°C	
Soldering recommendations (peak temperature) ^{d, e}		260			

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT	
Junction-to-ambient	R _{thJA}	85	85	°C/W	
Junction-to-case (drain)	R _{thJC}	5.5	3.1		

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	60	-	-
		$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	60	-	-
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	2.5	3.0	3.5
		$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	2.5	3.0	3.5
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		N-Ch 1	-	-	± 100
				N-Ch 2	-	-	± 100
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	N-Ch 1	-	-	1
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	N-Ch 2	-	-	1
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	-	50
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	-	50
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	-	250
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	-	250
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 1	15	-	-
		$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 2	30	-	-
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}$	N-Ch 1	-	0.0165	0.0200
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$	N-Ch 2	-	0.0071	0.0086
		$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	-	0.0320
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	-	0.0135
		$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	-	0.0390
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	-	0.0167
Forward transconductance ^b	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 6\text{ A}$		N-Ch 1	-	24	-
		$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$		N-Ch 2	-	98	-
Dynamic ^b							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	687	1000
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	1490	2100
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	313	500
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	777	1100
Reverse transfer capacitance	C_{rss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	10	15
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	21	30
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1.5\text{ A}$	N-Ch 1	-	9.2	16
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 3\text{ A}$	N-Ch 2	-	19.2	32
Gate-source charge ^c	Q_{gs}	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1.5\text{ A}$	N-Ch 1	-	3.2	-
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 3\text{ A}$	N-Ch 2	-	6.3	-
Gate-drain charge ^c	Q_{gd}	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1.5\text{ A}$	N-Ch 1	-	0.8	-
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 3\text{ A}$	N-Ch 2	-	1.5	-
Gate resistance	R_g	$f = 1\text{ MHz}$		N-Ch 1	0.35	0.74	1.20
				N-Ch 2	0.20	0.42	0.65



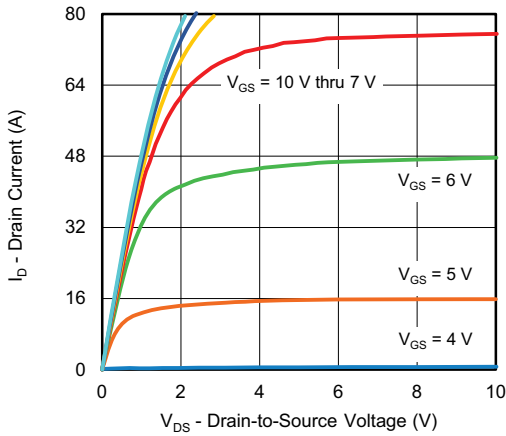
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Dynamic ^b							
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $R_L = 20\ \Omega$, $I_D \cong 1.5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	11	18	ns
		$V_{DD} = 30\text{ V}$, $R_L = 10\ \Omega$, $I_D \cong 3\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	12	25	
Rise time ^c	t_r	$V_{DD} = 30\text{ V}$, $R_L = 20\ \Omega$, $I_D \cong 1.5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	2	5	
		$V_{DD} = 30\text{ V}$, $R_L = 10\ \Omega$, $I_D \cong 3\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	3	5	
Turn-off delay time ^c	$t_{d(off)}$	$V_{DD} = 30\text{ V}$, $R_L = 20\ \Omega$, $I_D \cong 1.5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	16	30	
		$V_{DD} = 30\text{ V}$, $R_L = 10\ \Omega$, $I_D \cong 3\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	20	40	
Fall time ^c	t_f	$V_{DD} = 30\text{ V}$, $R_L = 20\ \Omega$, $I_D \cong 1.5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	8	15	
		$V_{DD} = 30\text{ V}$, $R_L = 10\ \Omega$, $I_D \cong 3\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	11	18	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I_{SM}		N-Ch 1	-	-	65	A
			N-Ch 2	-	-	90	
Forward voltage	V_{SD}	$I_F = 6\text{ A}$, $V_{GS} = 0\text{ V}$	N-Ch 1	-	0.82	1.2	V
		$I_F = 10\text{ A}$, $V_{GS} = 0\text{ V}$	N-Ch 2	-	0.80	1.2	
Body diode reverse recovery time	t_{rr}	$I_F = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	22	45	ns
		$I_F = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	41	85	
Body diode reverse recovery charge	Q_{rr}	$I_F = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	15	30	nC
		$I_F = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	36	75	
Reverse recovery fall time	t_a	$I_F = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	12	-	ns
		$I_F = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	19	-	
Reverse recovery rise time	t_b	$I_F = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	10	-	
		$I_F = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	22	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$	$I_F = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	-1.3	-	A
		$I_F = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	-1.6	-	

Notes

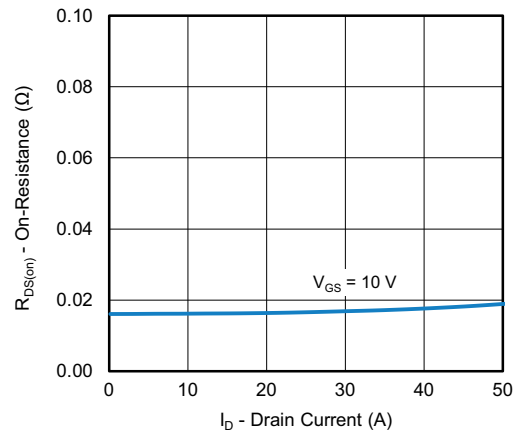
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

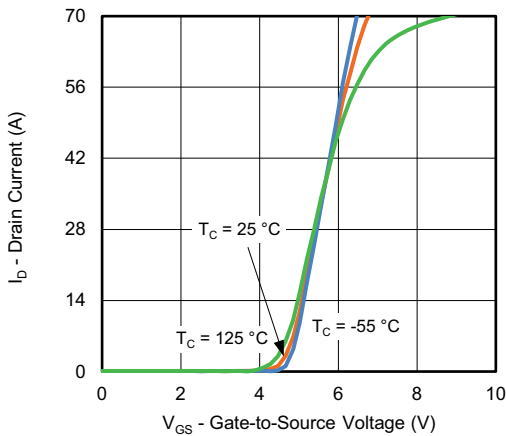
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



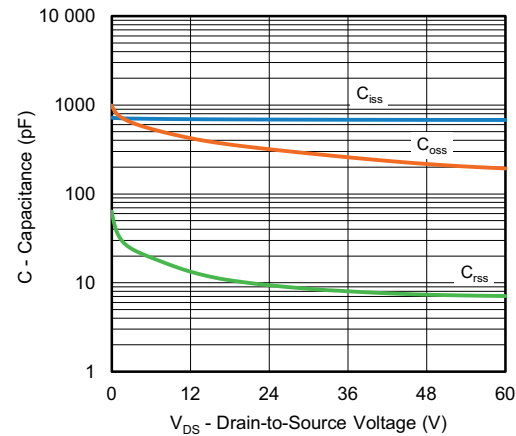
Output Characteristics



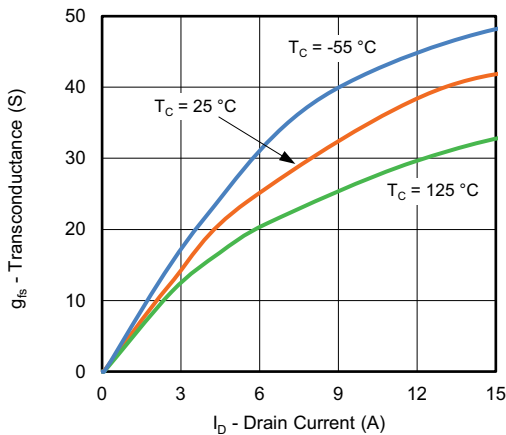
Transconductance



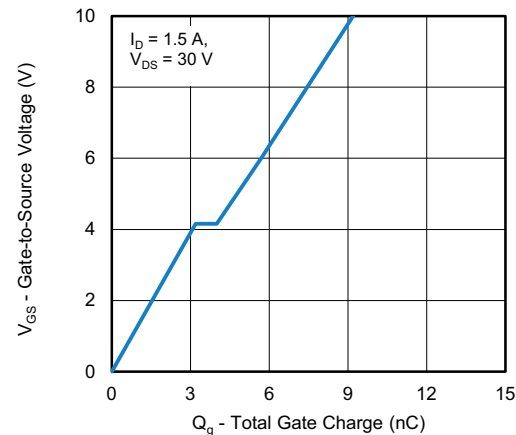
Transfer Characteristics



Capacitance



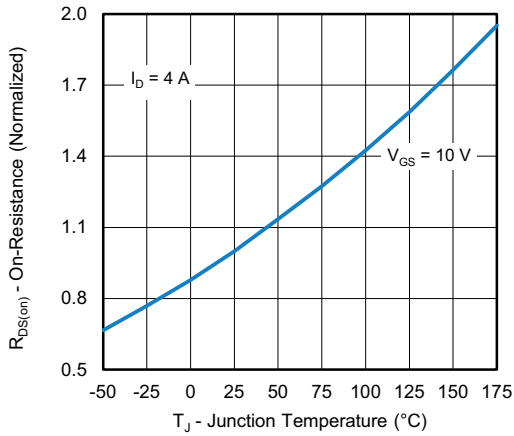
On-Resistance vs. Drain Current



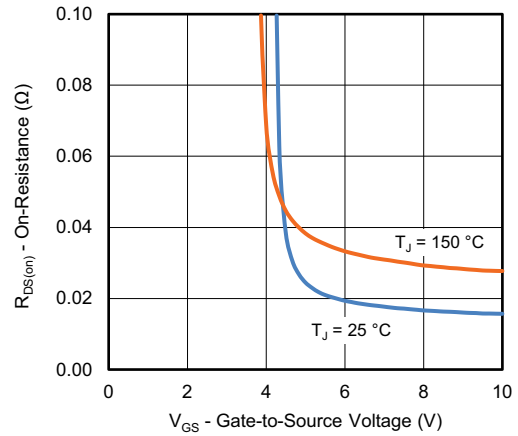
Gate Charge



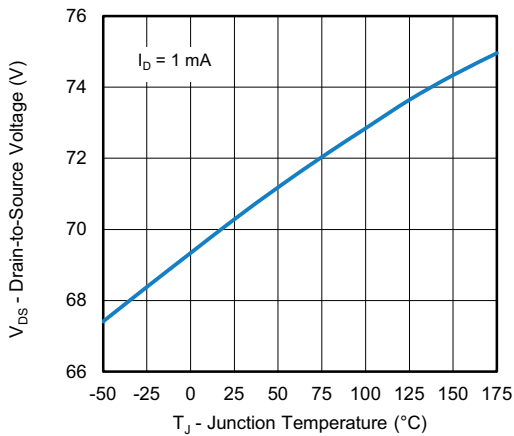
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



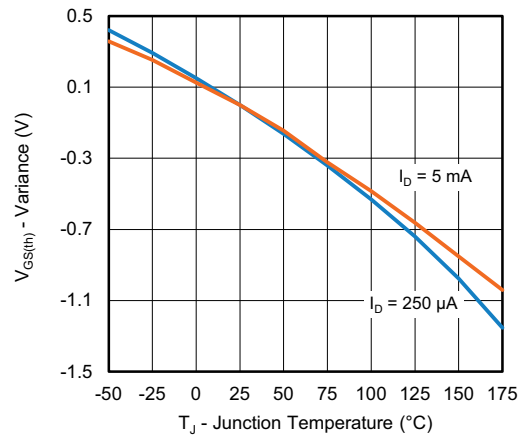
Source Drain Diode Forward Voltage



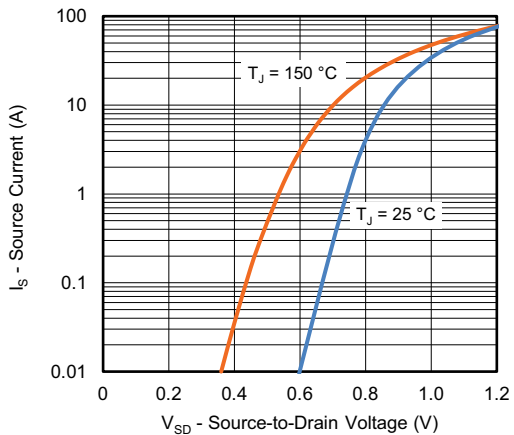
On-Resistance vs. Gate-to-Source Voltage



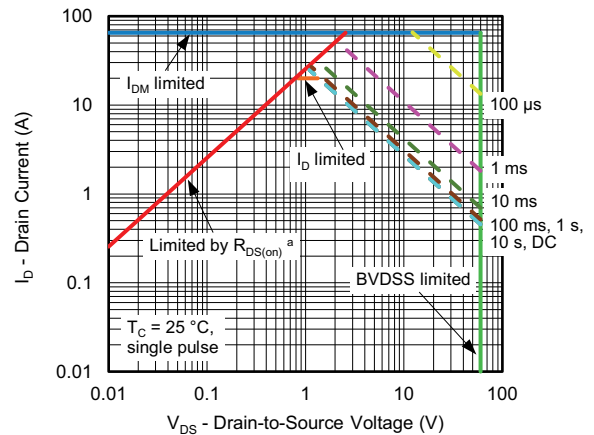
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

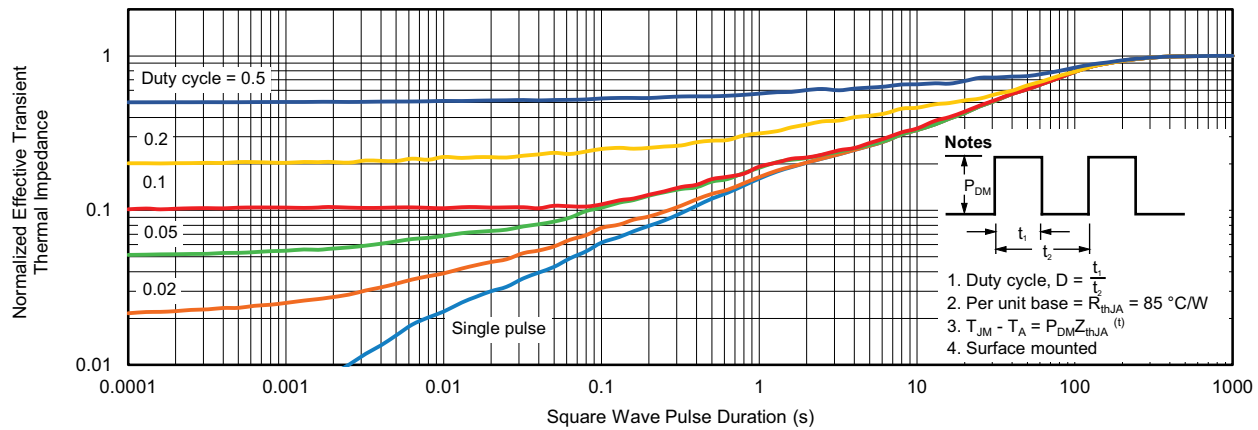


On-Resistance vs. Junction Temperature

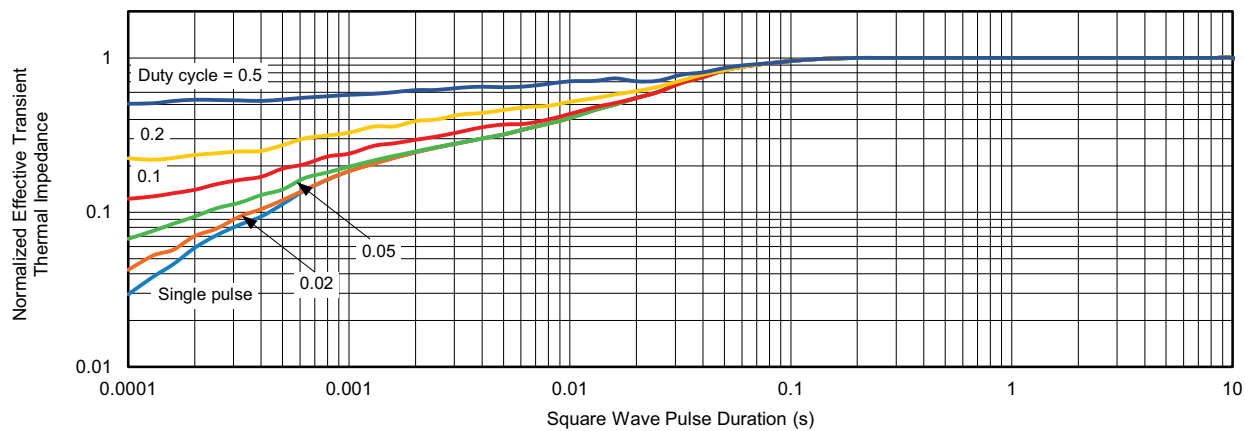


Safe Operating Area

N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



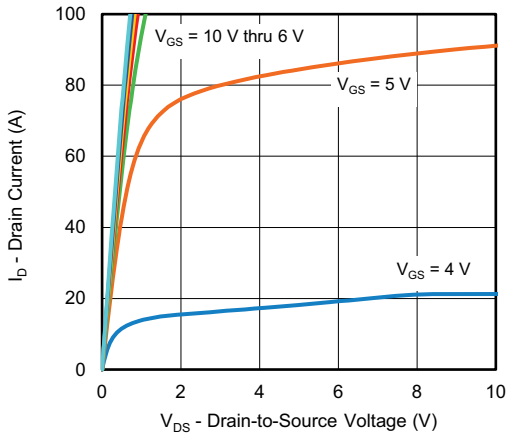
Normalized Thermal Transient Impedance, Junction-to-Case

Note

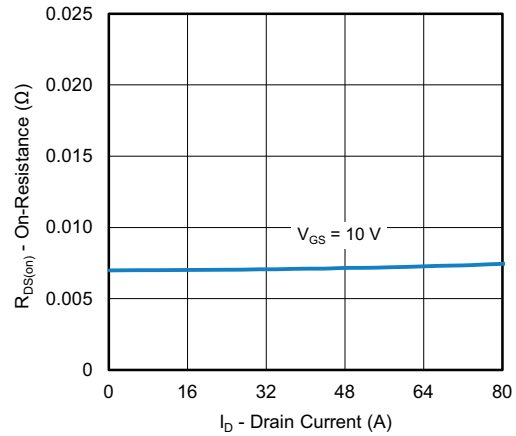
- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$) is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions



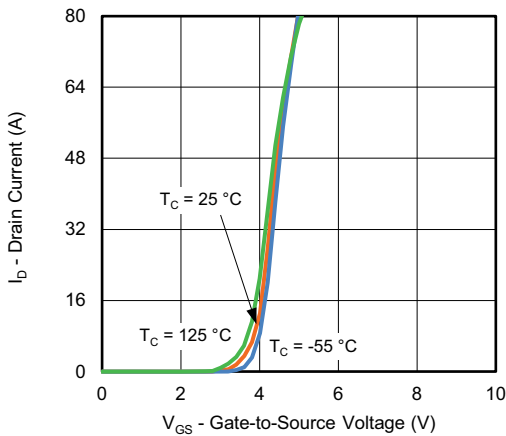
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



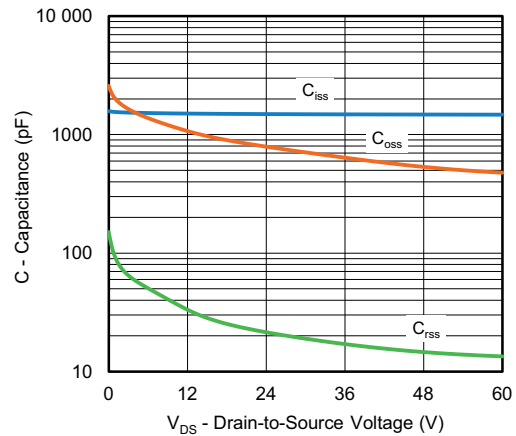
Output Characteristics



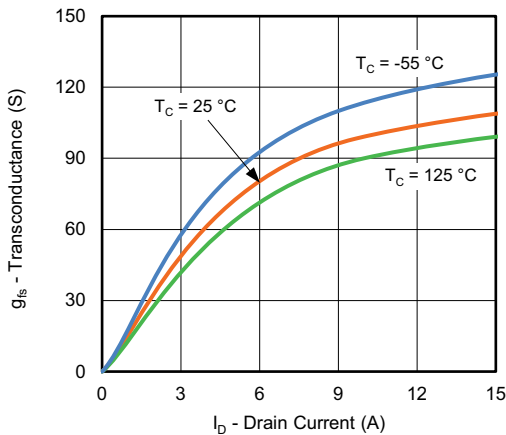
Transconductance



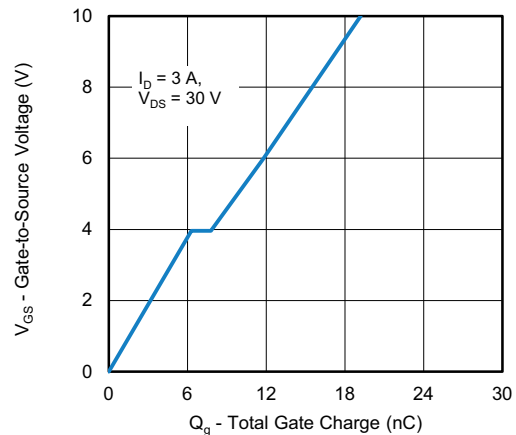
Transfer Characteristics



Capacitance

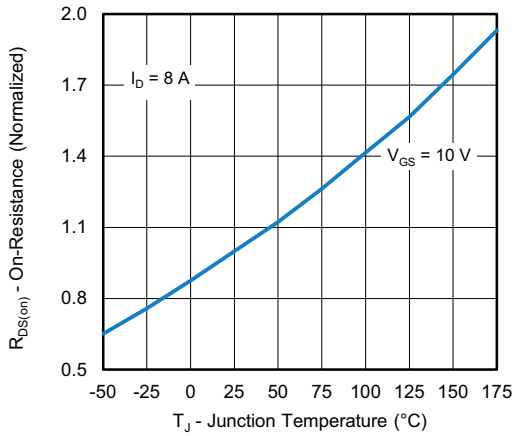


On-Resistance vs. Drain Current

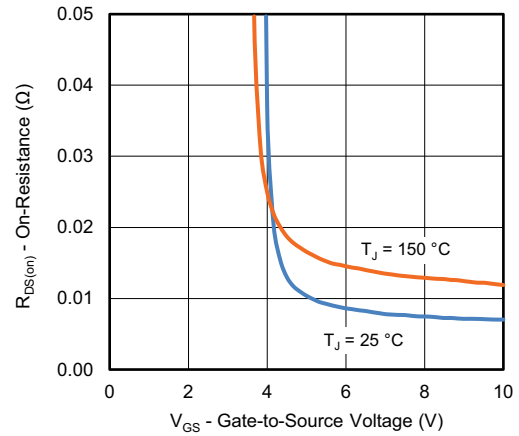


Gate Charge

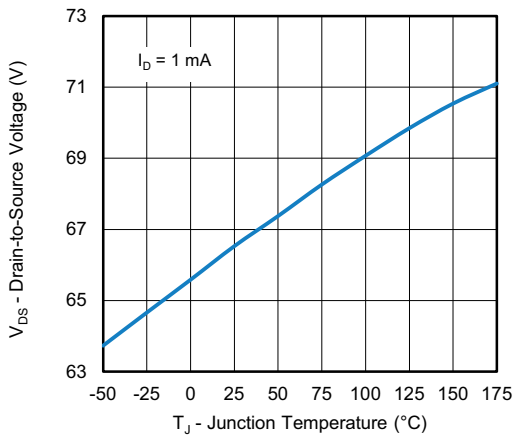
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



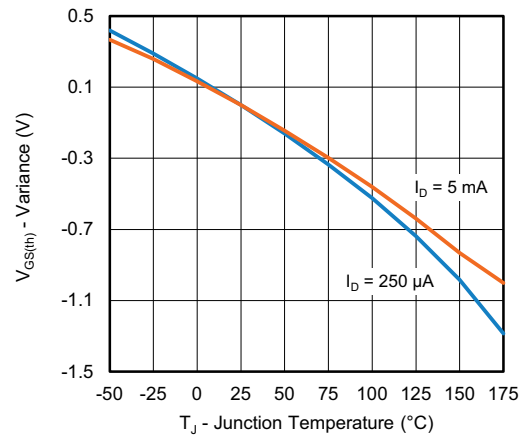
Source Drain Diode Forward Voltage



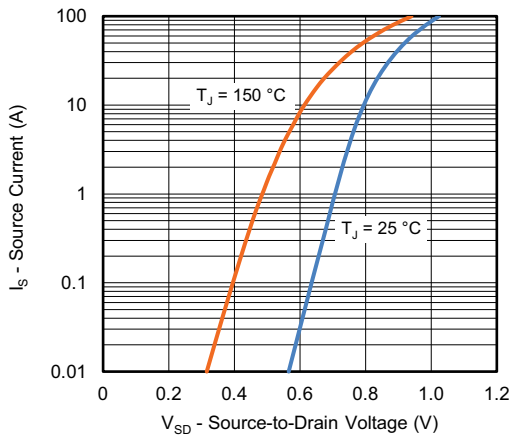
On-Resistance vs. Gate-to-Source Voltage



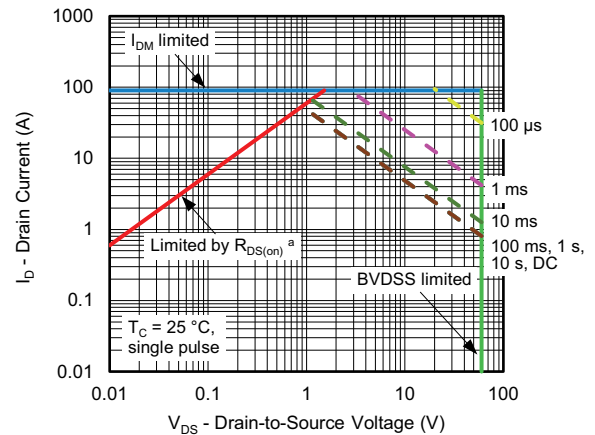
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

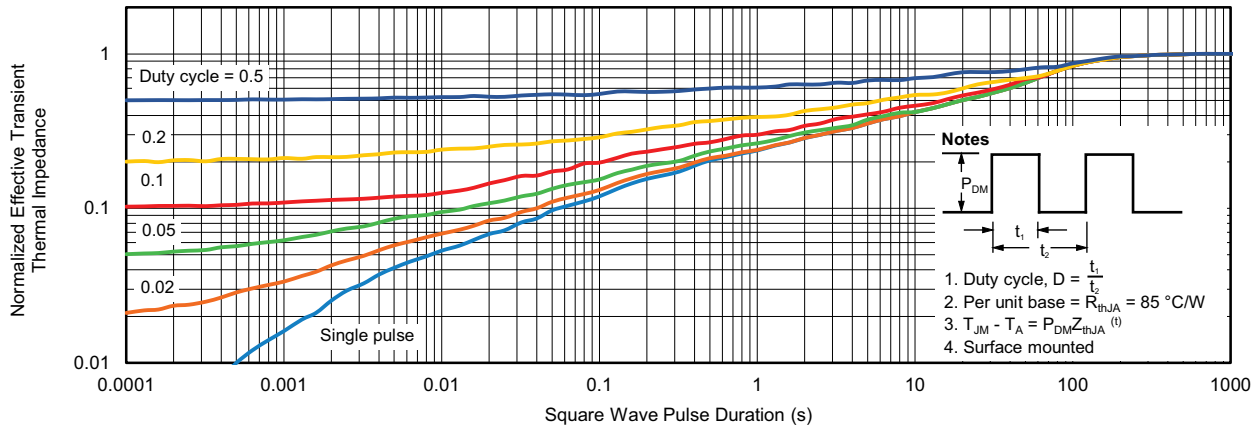


On-Resistance vs. Junction Temperature

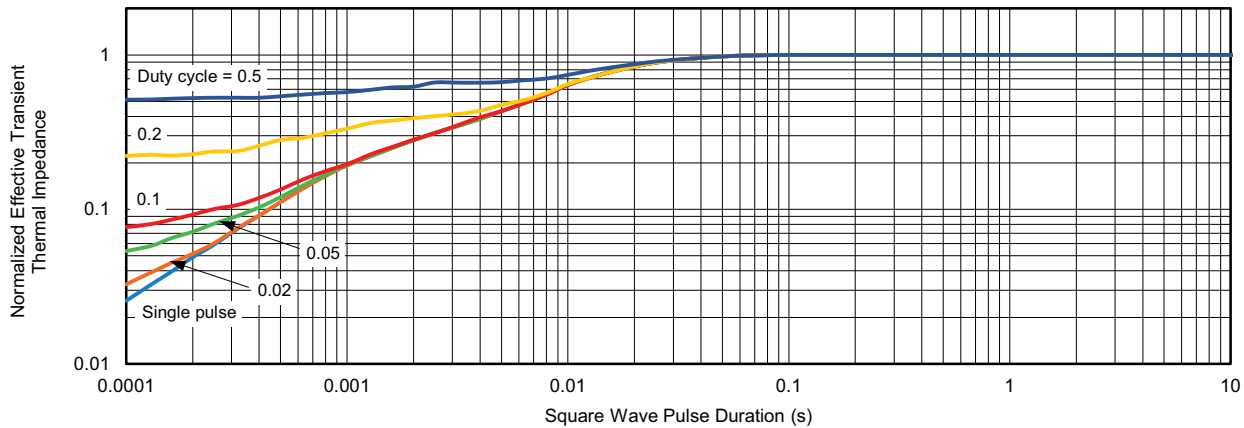


Safe Operating Area

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

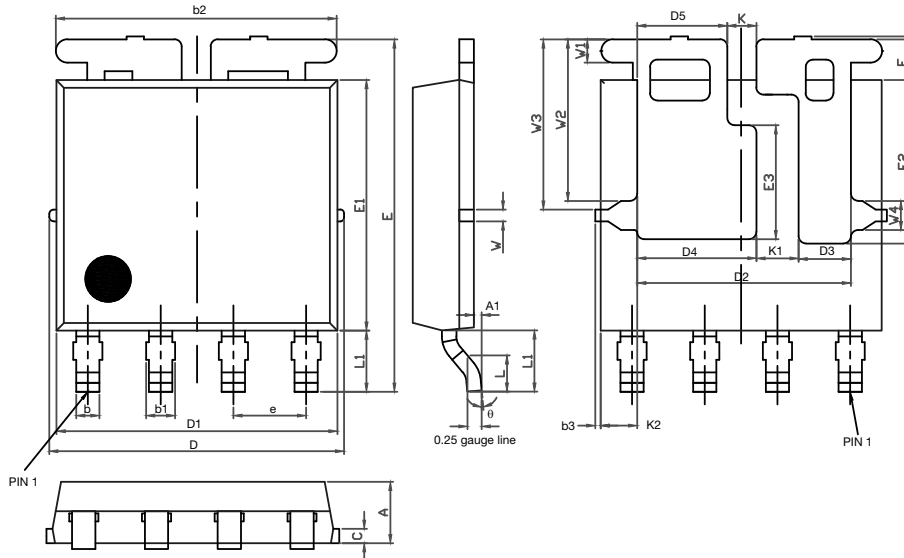
Note

- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$) is given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75486.



PowerPAK[®] SO-8L Assymmetric Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	0.06	0.13	0.000	0.003	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.04	0.12	0.20	0.002	0.005	0.008
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.63	3.73	3.83	0.143	0.147	0.151
D3	0.81	0.91	1.01	0.032	0.036	0.040
D4	1.98	2.08	2.18	0.078	0.082	0.086
D5	1.47	1.57	1.67	0.058	0.062	0.066
e	1.20	1.27	1.34	0.047	0.050	0.053
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
E3	1.89	1.99	2.09	0.074	0.078	0.082
F	0.05	0.12	0.19	0.002	0.005	0.007
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.41	0.51	0.61	0.016	0.020	0.024
K1	0.64	0.74	0.84	0.025	0.029	0.033
K2	0.54	0.64	0.74	0.021	0.025	0.029
W	0.13	0.23	0.33	0.005	0.009	0.013
W1	0.31	0.41	0.51	0.012	0.016	0.020
W2	2.72	2.82	2.92	0.107	0.111	0.115
W3	2.86	2.96	3.06	0.113	0.117	0.120
W4	0.41	0.51	0.61	0.016	0.020	0.024
θ	5°	10°	12°	5°	10°	12°

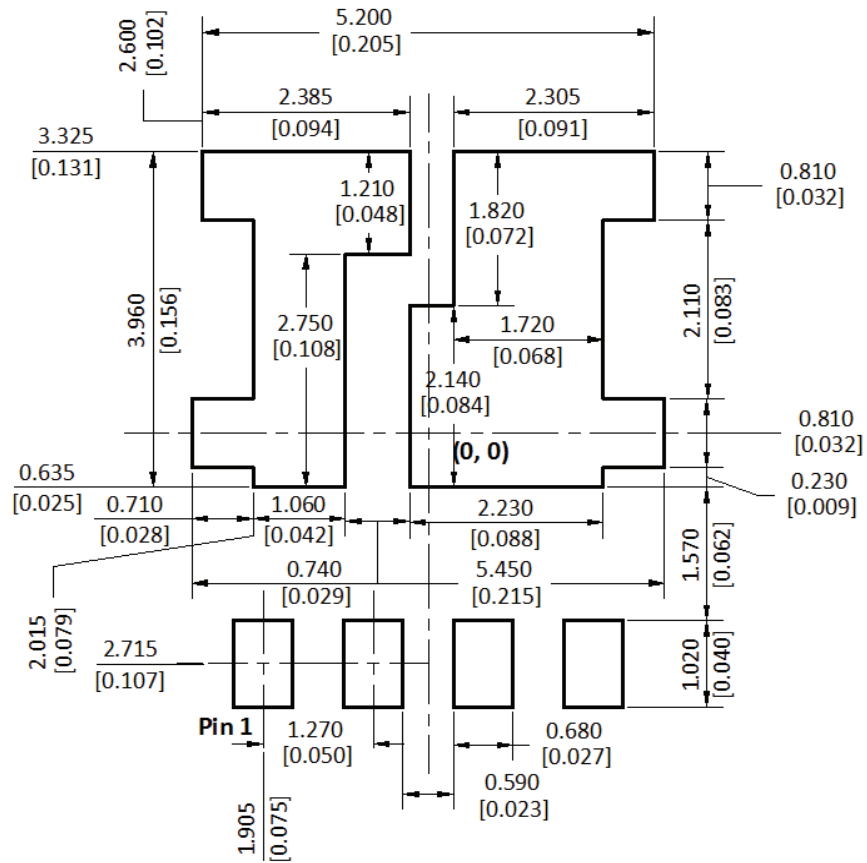
DWG: 6009

Note

- Millimeters will govern



RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8L DUAL ASYMMETRIC



Recommended Minimum Pads
Dimensions in mm [inches]



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